BTA310X-600D



3Q Hi-Com Triac
Rev. 1 — 23 April 2012

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with very sensitive gate
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

1.3 Applications

- Industrial and domestic heating circuits
- Motor controls e.g. washing machines and vacuum cleaners
- Refrigeration and air-conditioner compressor controls

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 ms$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	85	Α
Tj	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 73 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	10	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	0.3	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G -; T_j = 25 \text{ °C;}$ see Figure 7	0.3	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-; } T_j = 25 \text{ °C;}$ see Figure 7	0.3	-	5	mA
Dynamic c	haracteristics					
dV _D /dt	rate of rise of off-state voltage	ge V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V; } T_j = 125 \text{ °C; } I_{T(RMS)} = 10 \text{ A;}$ $dV_{com}/dt = 1 \text{ V/}\mu\text{s; gate open circuit}$	4.5	-	-	A/ms
•	· · · · · · · · · · · · · · · · · · ·					

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		. .
2	T2	main terminal 2	mb	T2—T1
3	G	gate		sym051
mb	n.c.	mounting base; isolated		
			SOT186A (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	number Package			
	Name	Description	Version	
BTA310X-600D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 73$ °C; see Figure 1; see Figure 2; see Figure 3	-	10	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	85	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	93	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	36.1	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 20 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_GM	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

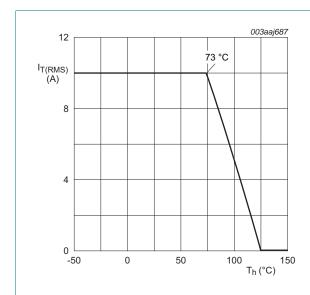
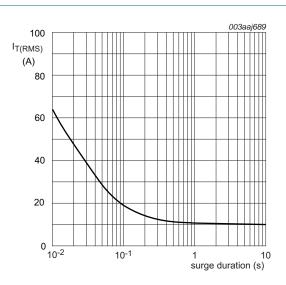


Fig 1. RMS on-state current as a function of heatsink temperature; maximum values



 $f = 50 \text{ Hz}; T_h = 73 \text{ }^{\circ}\text{C}$

Fig 2. RMS on-state current as a function of surge duration; maximum values

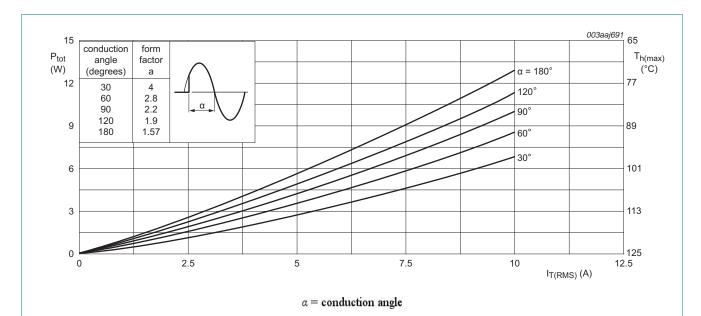


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

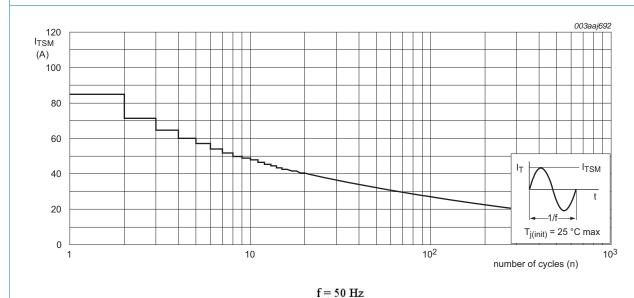
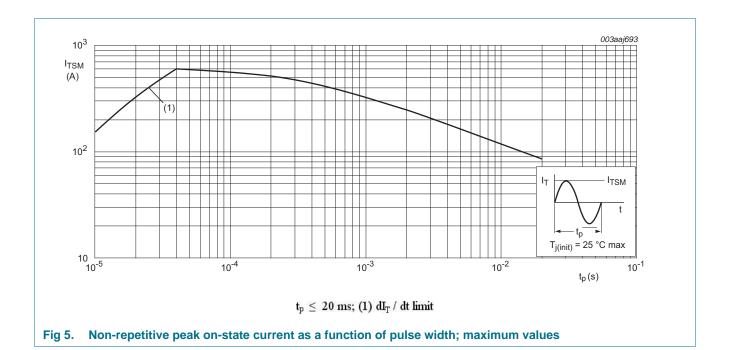


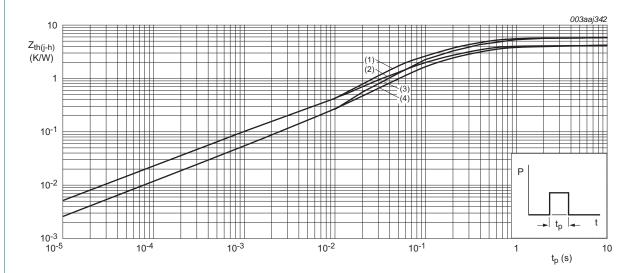
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$		full cycle or half cycle; with heatsink compound; see Figure 6	-	-	4	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

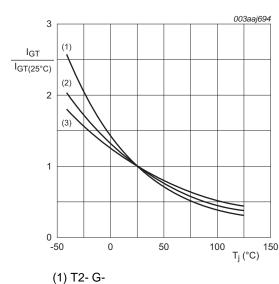
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1 \text{ MHz}$; $T_h = 25 ^{\circ}\text{C}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; T_j = 25 ^{\circ}\text{C};$ see Figure 7	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}\text{C};$ see Figure 7	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-}; T_j = 25 ^{\circ}\text{C};$ see Figure 7	0.3	-	5	mA
lL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 °C;$ see <u>Figure 8</u>	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	15	mA
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	-	10	mΑ
V _T	on-state voltage	I _T = 12 A; T _j = 25 °C; see <u>Figure 10</u>	-	1.25	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
I _D	off-state current	$V_D = 600 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	20	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 10 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	1	-	-	A/ms
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 10 A; dV_{com}/dt = 10 V/µs; gate open circuit	1.5	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 10 \text{ A};$ $dV_{com}/dt = 1 \text{ V}/\mu\text{s};$ gate open circuit	4.5	-	-	A/ms



- (2) T2+ G+
- (3) T2+ G-

Fig 7. Normalized gate trigger current as a function of junction temperature

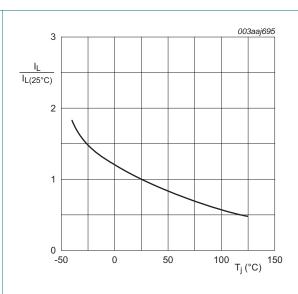
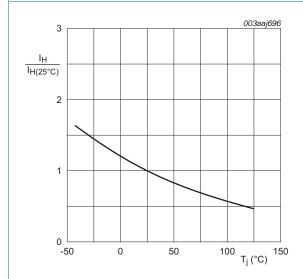
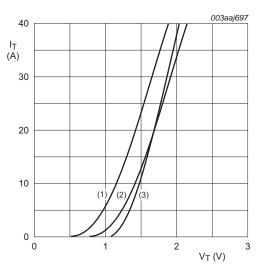


Fig 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of junction temperature



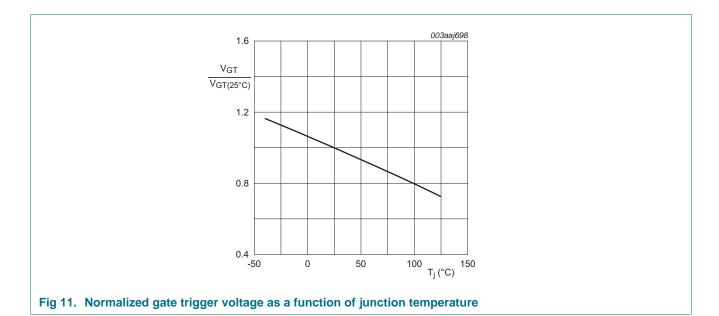
 $V_o = 1.103 \ V; \ R_s = 0.030 \ \Omega$

(1) T_i = 125 °C; typical values

(2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

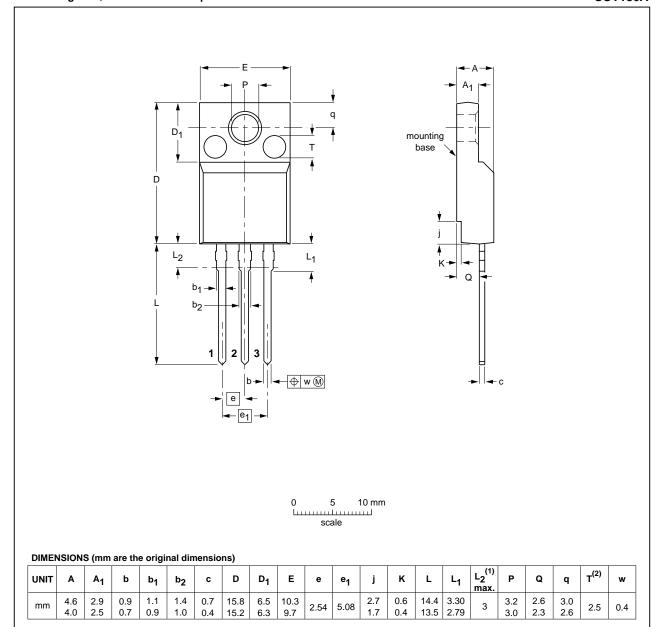
Fig 10. On-state current as a function of on-state voltage



8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

	OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION		IEC	JEDEC	JEITA		PROJECTION	1330E DATE
5	SOT186A		3-lead TO-220F				-02-04-09 06-02-14

Fig 12. Package outline SOT186A (TO-220F)

BTA310X-600D

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA310X-600D v.1	20120423	Product data sheet	-	-

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10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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